

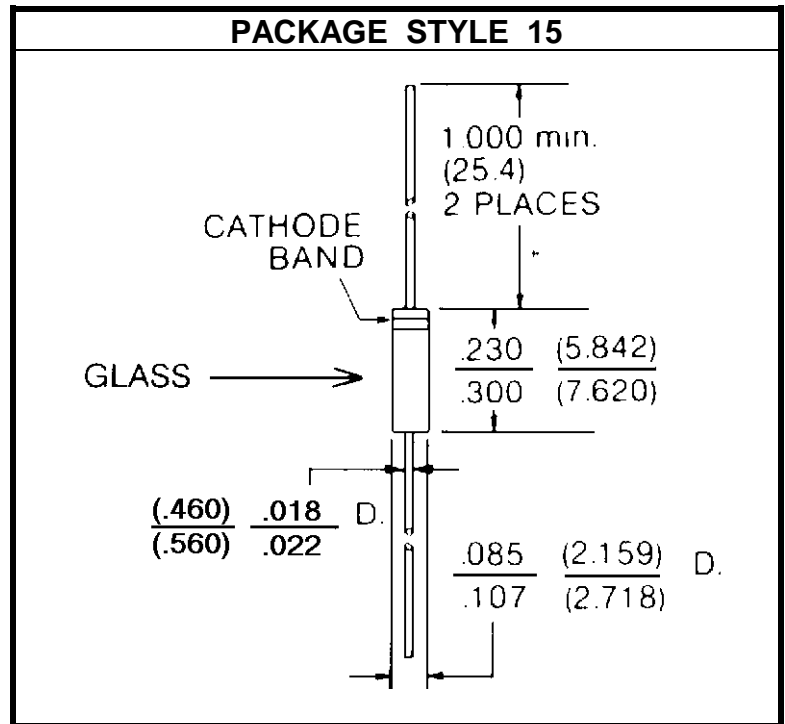
# SILICON PIN DIODE

**DESCRIPTION:**

The **ASI 5082-3081** PIN Diode is Designed for Low Power RF Switching and Attenuating Applications.

**MAXIMUM RATINGS**

<b>I</b>	250 mA
<b>V</b>	100 V
<b>P<sub>DISS</sub></b>	250 mW @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +150 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>T<sub>SOLD</sub></b>	260 °C for 5 sec.


**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V <sub>R</sub>	I <sub>R</sub> = 10 μA	100			V
V <sub>F</sub>	I <sub>F</sub> = 100 mA		1.0		V
τ	I <sub>F</sub> = 50 mA      I <sub>R</sub> = 250 mA		2500		nS
R <sub>S</sub>	I <sub>F</sub> = 100 mA      f = 100 MHz			3.5	Ω
C <sub>t</sub>	V <sub>R</sub> = 50 V      f = 1.0 MHz			0.4	pF
R <sub>H</sub>	I <sub>F</sub> = 10 μA      f = 100 MHz	1500			Ω
R <sub>L</sub>	I <sub>F</sub> = 20 mA      f = 100 MHz			8.0	Ω